

INFORMATION DISCLOSURE
CITATION

ATTY. DOCKET NO.

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925-178

09/463,643

APPLICANT

NAKAMURA et al.

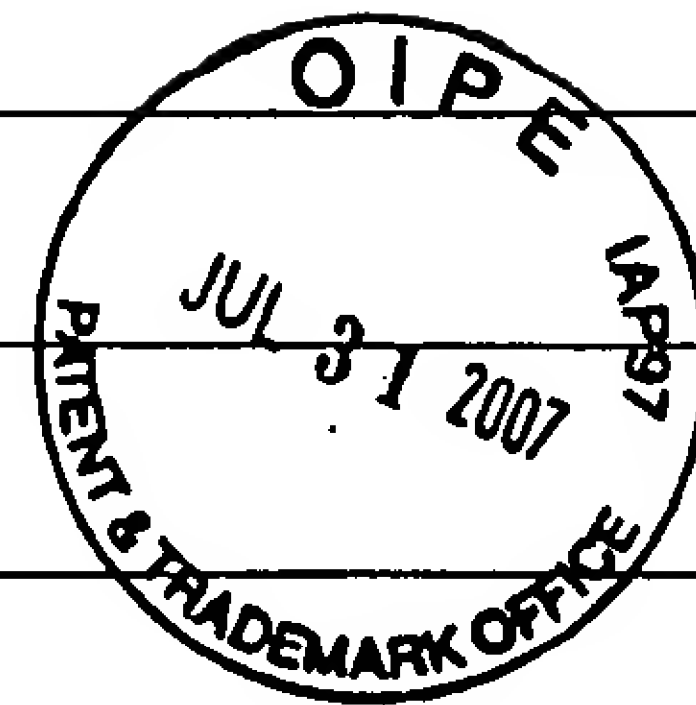
FILING DATE

GROUP

May 1, 2000

2815

(Use several sheets if necessary)



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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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*Examiner

Date Considered

10/07/07

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Sheet 11 of 11		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No.: NICHIA-00700	Serial No.:09/463643
FORM PTO-1449 (Modified)		INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR § 1.98(b))		Applicant: Shuji Nakamura, et al.	
				Filing Date: January 25, 2000	Group Art Unit:

NS	WO9857378A1	12/17/98	PCT	HOIL	29/73	
NT	WO9910936A2	3/4/99	PCT	HOIL	33/00	
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